

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

# 2. Features and benefits

- Extended temperature range T<sub>i</sub> = 175 °C
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Tin-plated 100% solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1.5 kV HBM
- Trench MOSFET technology
- AEC-Q101 qualified

# 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

# 4. Quick reference data

### Table 1. Quick reference data

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	3.8	А
Static characte	ristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.8 A; T <sub>j</sub> = 25 °C		-	55	72	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

# nexperia

# 5. Pinning information

Fable 2. Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	D	drain		
3	G	gate		
4	S	source		G ( The second s
5	D	drain	3 8 4	
6	D	drain	Transparent top view	
7	D	drain	DFN2020MD-6 (SOT1220)	S 0470000555
8	S	source		017aaa255

# 6. Ordering information

# Table 3. Ordering information Type number Package Name Description Version BUK4D72-30 DFN2020MD-6 plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body SOT1220

# 7. Marking

Table 4.	Marking	codes
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Type number	Marking code
BUK4D72-30	6G

30 V, N-channel Trench MOSFET

# 8. Limiting values

### Table 5. Limiting values

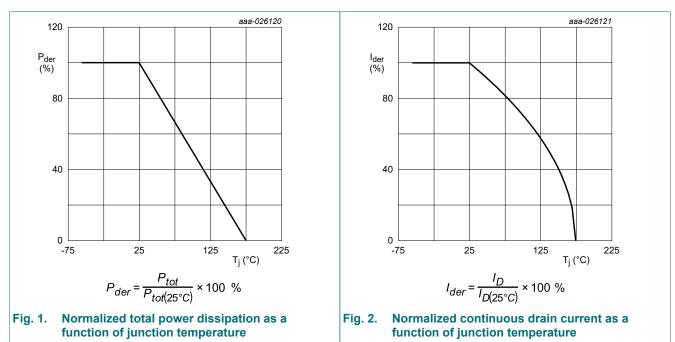
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
ID	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	3.8	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	2.4	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	16	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	550	mW
			[1]	-	1.95	W
		T <sub>sp</sub> = 25 °C		-	10	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 0.3 A; DUT in avalanche (unclamped)		-	6.2	mJ
Source-drain	diode		•			
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.9	А
ESD maximu	m rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	1500	V

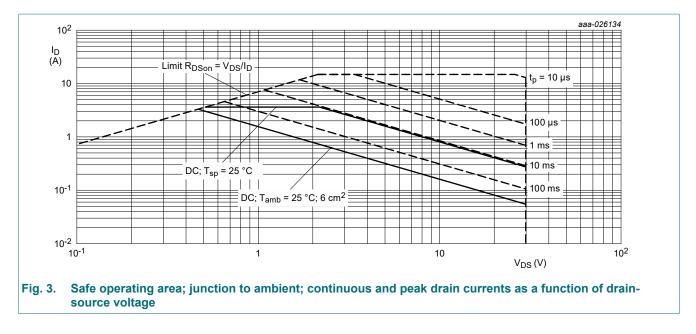
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4[3] Measures between all pins.



### 30 V, N-channel Trench MOSFET



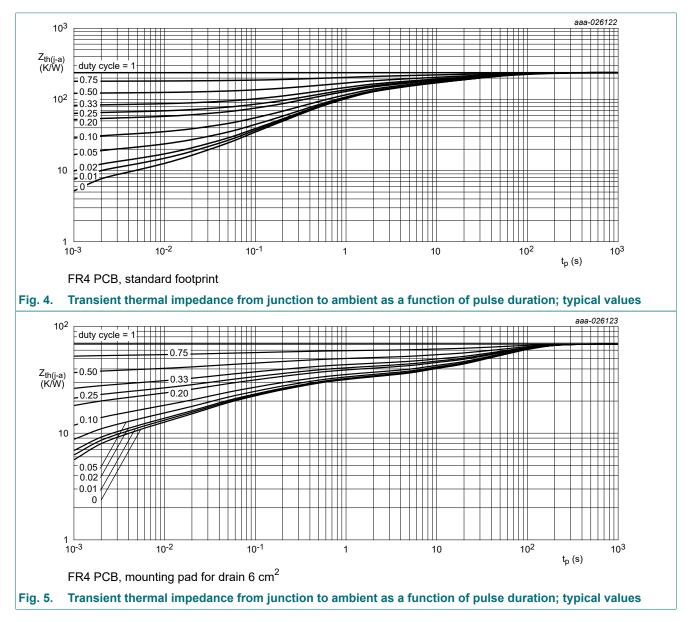
BUK4D72-30

# 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	in free air	[1]	-	236	272	K/W	
		[2]	-	67	77	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	12	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

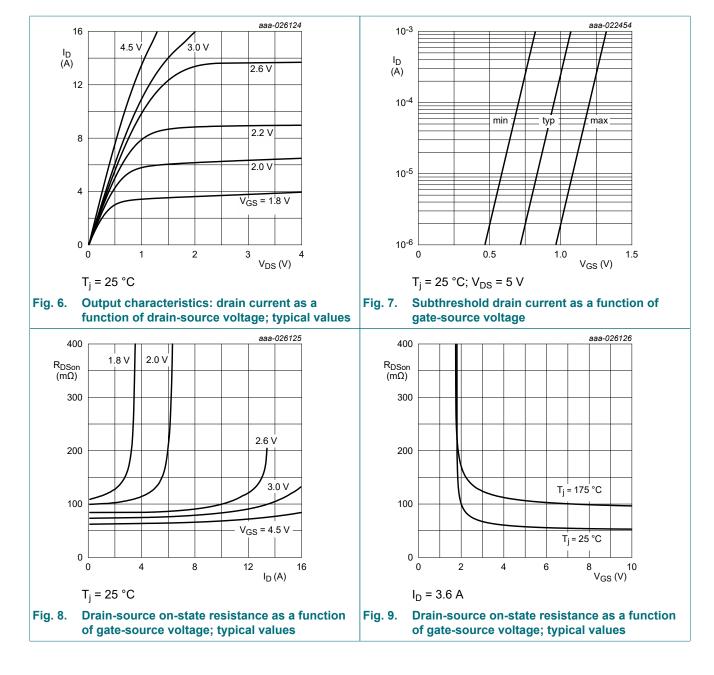
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



# **10. Characteristics**

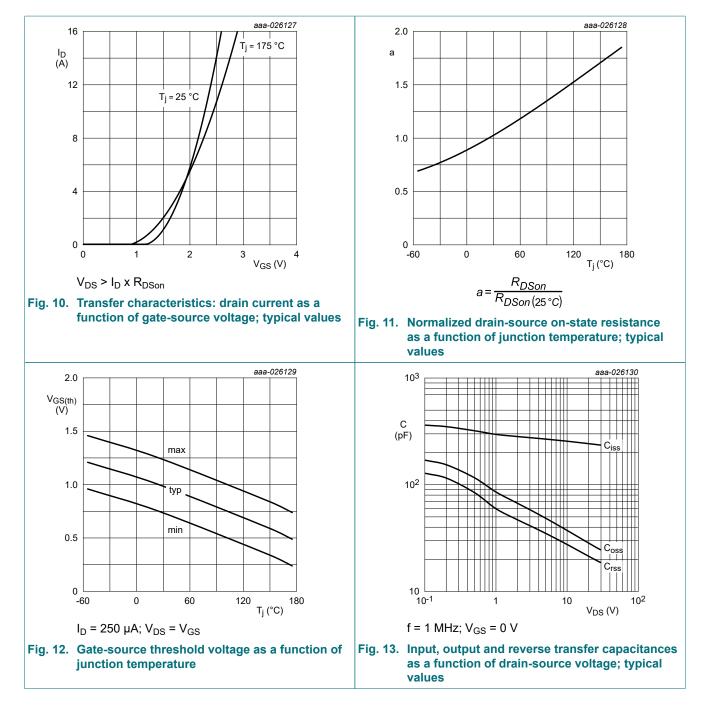
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	0.75	1	1.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.8 A; T <sub>j</sub> = 25 °C	-	55	72	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.8 A; T <sub>j</sub> = 175 °C	-	102	133	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 25 °C	-	77	110	mΩ
9fs	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3.8 A; T <sub>j</sub> = 25 °C	-	20	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	10.8	-	Ω
Dynamic ch	aracteristics	1				
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 3.6 A; V <sub>GS</sub> = 4.5 V;	-	3	5	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.5	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	0.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	255	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	31	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	23	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 3.6 A; V <sub>GS</sub> = 4.5 V;	-	7	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	20	-	ns
t <sub>d(off)</sub>	turn-off delay time	1 [	-	18	-	ns
t <sub>f</sub>	fall time	1	-	8	-	ns
Source-drai	n diode		1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.9 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 2.5 A; dI <sub>S</sub> /dt = -100 A/µs;	-	12.6	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 10 V; T <sub>j</sub> = 25 °C	-	4	-	nC

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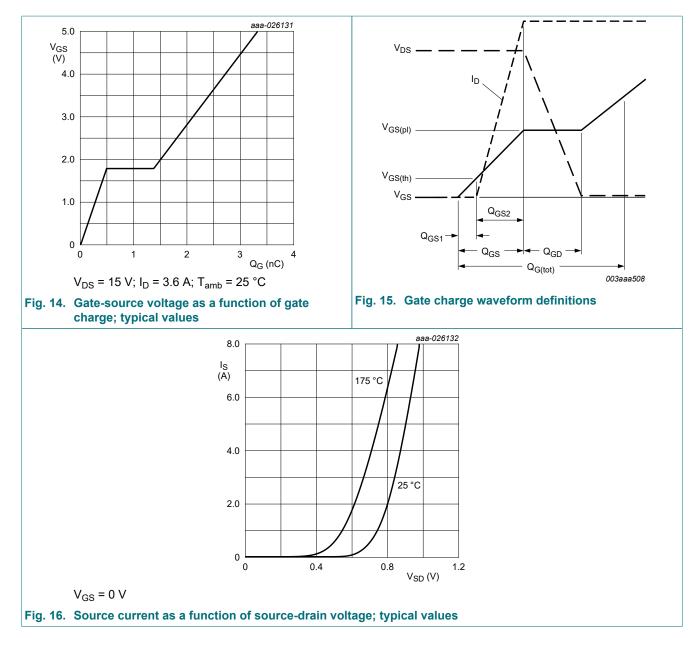


**Product data sheet** 

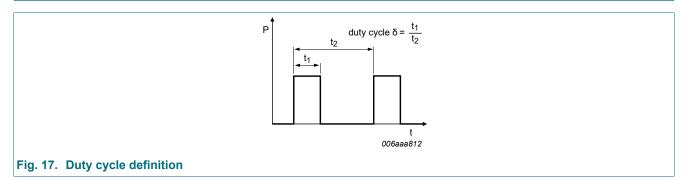
### 30 V, N-channel Trench MOSFET



### 30 V, N-channel Trench MOSFET



# **11. Test information**

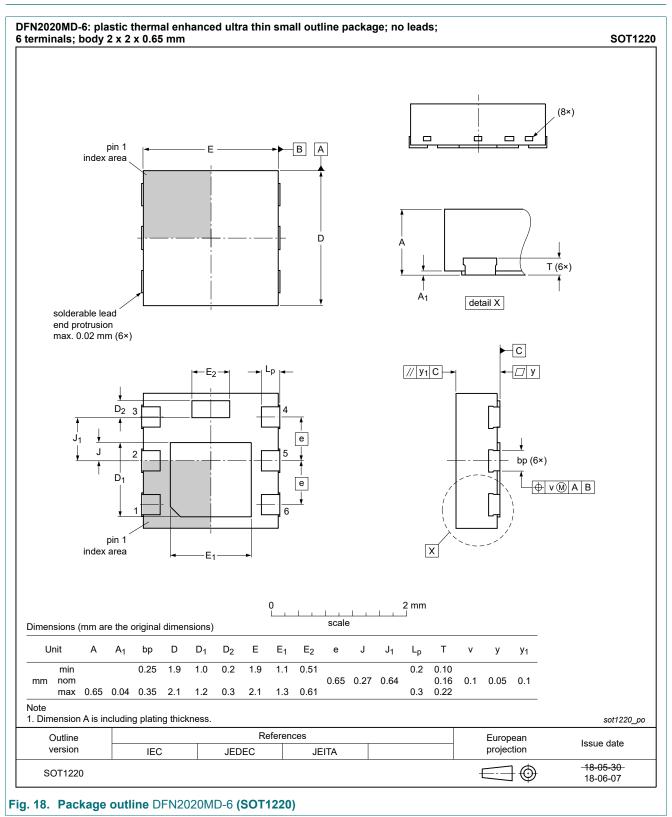


### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

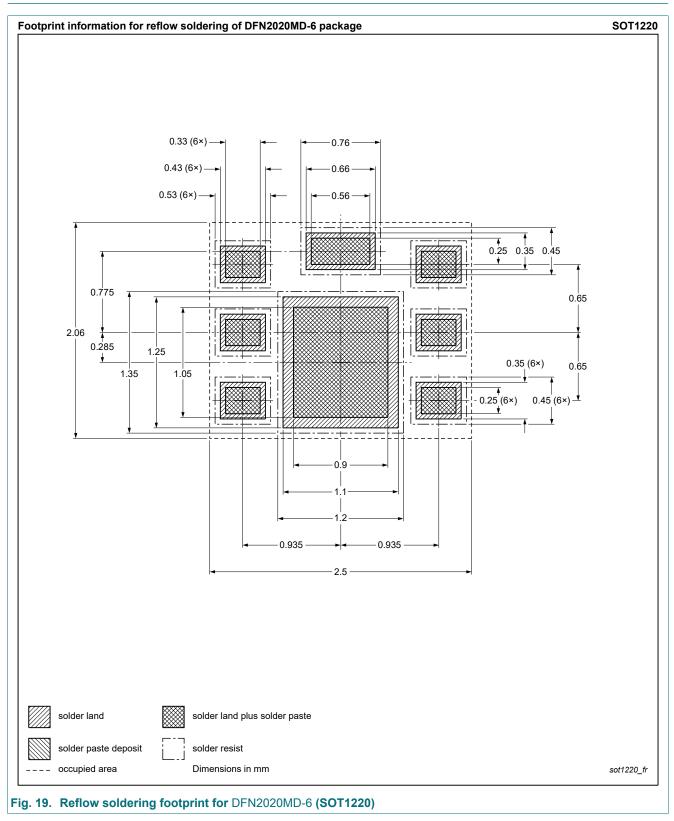
BUK4D72-30

# 12. Package outline



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# 13. Soldering



# 14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BUK4D72-30 v.2	20230327	Product data sheet	-	BUK4D72-30 v.1			
Modifications:	Complete rework	·					
BUK4D72-30 v.1	20200708	Product data sheet	-	-			

# 15. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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